

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK2013

Audio Frequency Power Amplifier Application

• High breakdown voltage : $V_{DSS} = 180V$ • High forward transfer admittance : $|Y_{fs}| = 0.7 \text{ S (typ.)}$

• Complementary to 2SJ313

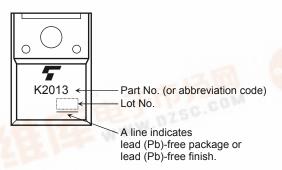
Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V _{DSS}	180	V
Gate-source voltage	V _{GSS}	±20	V
Drain current (Note 1)	I _D	1	Α
Drain power dissipation (Tc = 25°C)	P_{D}	25	W
Channel temperature	T _{ch}	150	°C
Storage temperature range	T _{stg}	-55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Weight: 1.9 g (typ.)

Marking



Electrical Characteristics (Ta = 25°C)

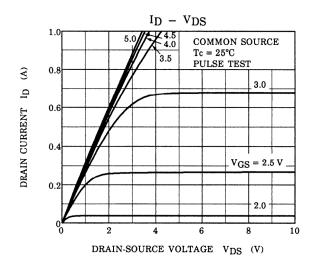
•	,					-0.10
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V _{DS} = 0, V _{GS} = ±20 V	74	_	±100	nA
Drain-source breakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0	180	_	_	V
Gate-source cut-off voltage (Note 2)	V _{GS} (OFF)	V _{DS} = 10 V, I _D = 10 mA	1.8	_	2.8	V
Drain-source saturation voltage	V _{DS} (ON)	I _D = 0.6 A, V _{GS} = 10 V	_	1.7	3.0	V
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, I _D = 0.3 A	_	0.7	_	S
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz	_	170	_	
Output capacitance	Coss	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz	_	45	_	pF
Reverse transfer capacitance	C _{rss}	V _{DD} ≈ 10 V, V _{GS} = 0, f = 1 MHz	_	17	_	

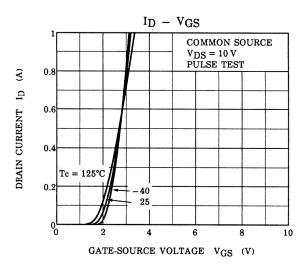
Note 1: Ensure that the channel temperature does not exceed 150°C.

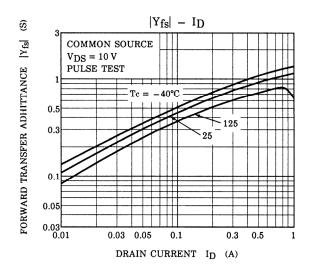
Note 2: V_{GS (OFF)} Classification O: 0.8~1.6, Y: 1.4~2.8

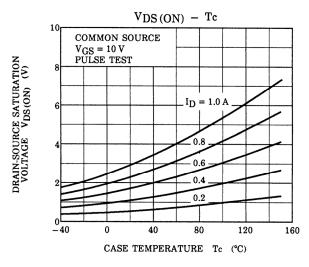
This transistor is an electrostatic-sensitive device.

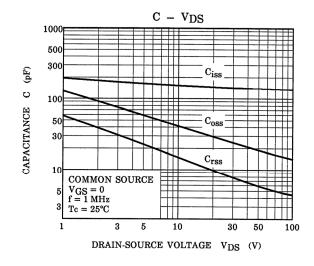
Please handle with caution.

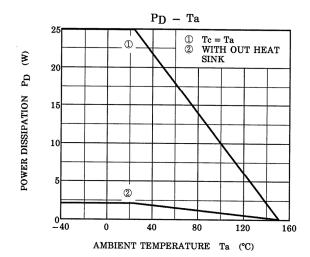


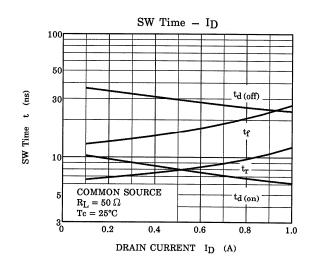


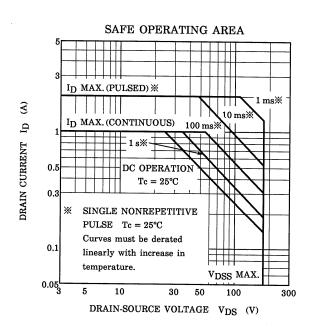




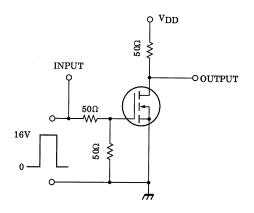




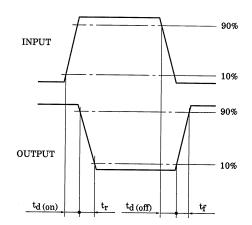




Switching Time Test Circuit



Waveforms



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20070701-EN

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